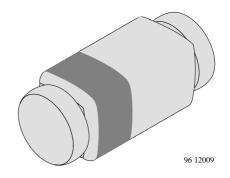


Small Signal Schottky Barrier Diode

Features

- Integrated protection ring against static discharge
- Very low forward voltage



Applications

Applications where a very low forward voltage is required

Order Instruction

Type	Type Differentiation	Ordering Code	Remarks
BAS285	$V_{R} = 30 \text{ V}$	BAS285-GS08	Tape and Reel

Absolute Maximum Ratings

 $T_i = 25^{\circ}C$

J					
Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage			V_R	30	V
Peak forward surge current	$t_p = 10 \text{ ms}$		I _{FSM}	5	Α
Repetitive peak forward current	t _p ≤ 1 s		I _{FRM}	300	mΑ
Forward current			I _F	200	mA
Average forward current			I _{FAV}	200	mA
Junction temperature			Tį	125	°C
Storage temperature range			T _{sta}	<i>−</i> 65+150	°C

Maximum Thermal Resistance

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Symbol	Value Uni		
Junction ambient	on PC board 50 mmx50 mmx1.6 mm	R _{th.IA}	320	K/W	

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Electrical Characteristics

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Type	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =0.1mA		V_{F}			240	mV
	I _F =1mA		V_{F}			320	mV
	I _F =10mA		V_{F}			400	mV
	I _F =30mA		V_{F}			500	mV
	I _F =100mA		V_{F}			800	mV
Reverse current	V _R =25 V, t _p =300μs		I _R			2.3	μΑ
Diode capacitance	V _R =1 V, f=1MHz		C_D			10	pF

Characteristics $(T_i = 25^{\circ}C \text{ unless otherwise specified})$

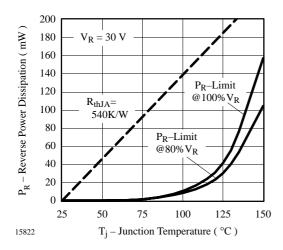


Figure 1. Max. Reverse Power Dissipation vs.
Junction Temperature

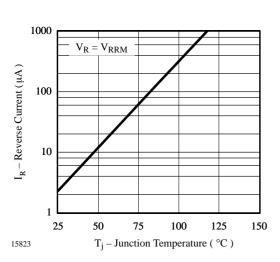


Figure 2. Reverse Current vs. Junction Temperature

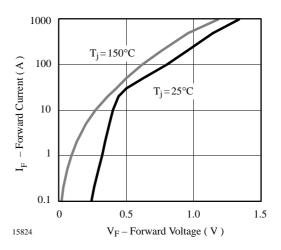


Figure 3. Forward Current vs. Forward Voltage

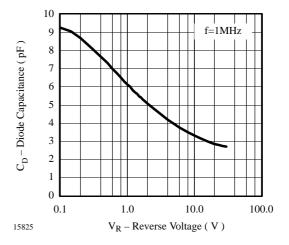


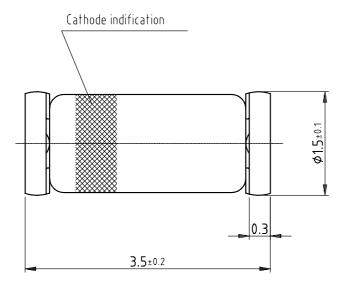
Figure 4. Diode Capacitance vs. Reverse Voltage

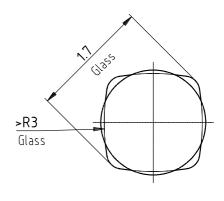




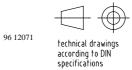
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Dimensions in mm





Glass case Quadro MELF / SOD80 similar to JEDEC 213 AA



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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